Koichi Maezawa

List of Publications by Year
in descending order

187	2,721	304743	254184
papers	citations	22 h-index	43 g-index

190	190	190	1383
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Experimental demonstration of a hard-type oscillator using a resonant tunneling diode and its comparison with a soft-type oscillator. IEICE Transactions on Electronics, 2021, , .	0.6	0
2	Transition Dynamics of Multistable Tunnel-Diode Oscillator Used for Effective Amplitude Modulation. IEICE Transactions on Electronics, 2021, E104.C, 40-43.	0.6	0
3	Noise Floor Reduction in Frequency Delta-Sigma Modulation Microphone Sensors. Sensors, 2021, 21, 3470.	3.8	2
4	Effects of Oscillator Phase Noise on Frequency Delta Sigma Modulators with a High Oversampling Ratio for Sensor Applications. IEICE Transactions on Electronics, 2021, E104.C, 463-466.	0.6	4
5	Coplanar waveguides fabricated by directly bonding metal foils to high-resistivity Si substrates. , 2021, , .		0
6	Delta-sigma modulation microphone sensors employing a resonant tunneling diode with a suspended microstrip resonator. Sensor Review, 2020, 40, 535-542.	1.8	4
7	Low-Loss Characteristics of Metal-Foil-Based Passive Components by Surface-Activated Bonding Technologies. IEEE Transactions on Electron Devices, 2019, 66, 3946-3952.	3.0	5
8	Study on impedance matching and maximum wireless power transfer efficiency of circuits with resonant coupling based on simplified S-matrix. IEICE Electronics Express, 2019, 16, 20190156-20190156.	0.8	6
9	Effect of flux ratio on GaSb films grown at a low temperature on Si(111). , 2019, , .		0
10	An investigation of the crystalline nature for GaSb films on Si(111) at varied growth temperature and growth rate. Japanese Journal of Applied Physics, 2019, 58, SIIA17.	1.5	3
11	Experimental observation of synchronised oscillating edges in electrical lattice with seriesâ€connected tunnel diodes. Electronics Letters, 2019, 55, 14-16.	1.0	3
12	Growth Nature of InSb Channel Layer on Heteroepitaxial Films of InGaSb Layer on GaSb/Si(111)-âˆš3 Ã—âˆš3-Ga Surface Phase. E-Journal of Surface Science and Nanotechnology, 2018, 16, 20-26.	0.4	3
13	A wide-range variable-frequency resonant tunneling diode oscillator using a variable resonator suitable for simple MEMS process. Japanese Journal of Applied Physics, 2018, 57, 04FG10.	1.5	0
14	Fullâ€wave analysis of traveling pulses developed in a system of transmission lines with regularly spaced resonantâ€tunneling diodes. International Journal of Circuit Theory and Applications, 2018, 46, 671-682.	2.0	4
15	Characterization of a hard-type oscillator using series-connected tunnel diodes. IEICE Electronics Express, 2018, 15, 20180355-20180355.	0.8	6
16	Possibilities of Large Voltage Swing Hard-Type Oscillators Based on Series-Connected Resonant Tunneling Diodes. IEICE Transactions on Electronics, 2018, E101.C, 305-310.	0.6	8
17	Large-amplitude voltage edge oscillating in a transmission line with regularly spaced series-connected resonant-tunneling diodes. IEICE Electronics Express, 2018, 15, 20180678-20180678.	0.8	3
18	Heteroepitaxial growth of InGaSb on GaSb/Si(111)â€“âˆš3â€‰Ã—â€‰âˆš3â€Ga surface phase with a twoâ€step growth method to investigate the impact of highâ€quality GaSb buffer layer. Physica Status Solidi (B): Basic Research, 2017, 254, 1600528.	1.5	5

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19	Experimental demonstration of strain detection using resonant tunneling deltaâ€sigma modulation sensors. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600548.	1.8	10
20	Al-foil-based low-loss coplanar waveguides directly bonded to sapphire substrates. , 2017, , .		2
21	Experimental demonstration of strain detection using resonant tunneling delta-sigma modulation sensors. , 2016, , .		0
22	Deltaâ€sigma modulation microphone sensors using microwave cavity resonator. Electronics Letters, 2016, 52, 1651-1652.	1.0	7
23	Effect of growth condition of buffer layer for heteroepitaxial InSb films grown on Ge(111) substrate. , 2016, , .		0
24	Resonant Tunneling Super Regenerative Detectors Detecting Higher Frequency Signals than Their Free-Running Oscillation Frequency. IEICE Transactions on Electronics, 2015, E98.C, 260-266.	0.6	0
25	Heteroepitaxial growth of InSb thin films on a Ge(111) substrate. , 2014, , .		0
26	Electrical characterization of n⁺-InSb/p-Si heterojunctions grwon by surface reconstruction controlled epitaxy. , 2014, , .		0
27	Ultrashort pulse generators using resonant tunneling diodes with improved power performance. , 2013, , .		0
28	Effective Mobility Enhancement in Al₂O₃/InSb/Si Quantum Well Metal Oxide Semiconductor Field Effect Transistors for Thin InSb Channel Layers. Japanese Journal of Applied Physics, 2013, 52, 04CF01.	1.5	7
29	Fluidic Self-Assembly Using Molten Ga Bumps and Its Application to Resonant Tunneling Diodes. Japanese Journal of Applied Physics, 2013, 52, 116501.	1.5	1
30	MEMS microphones on InP substrates for high performance digital ultrasonic sensors. , 2013, , .		0
31	Low resistance ohmic contacts to n-InSb employing Sn-alloys. , 2013, , .		0
32	Possibility of THz detection with resonant tunneling super regenerative detectors based on extremely high order harmonics. IEICE Electronics Express, 2013, 10, 20130676-20130676.	0.8	1
33	Fabrication and Characterization of Micromachined Cantilever Loaded with a Resonant Tunneling Diode for Delta-Sigma Type Strain Sensor Applications. , 2013, , .		1
34	Al<inf>2</inf>O<inf>3</inf>/InSb/Si quantum well MOSFETs having an ultra-thin InSb layer. , 2012, , .		1
35	Effects of Initial In Coverage for Preparation of InSb Bilayer on Electrical Properties of InSb Films Grown By Surface Reconstruction Controlled Epitaxy. Japanese Journal of Applied Physics, 2012, 51, 02BH03.	1.5	5
36	Characterization of Al2O3/InSb/Si MOS diodes having various InSb thicknesses grown on Si(1 1 1) substrates. Semiconductor Science and Technology, 2012, 27, 045007.	2.0	7

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37	Possibility of High Order Harmonic Oscillators Based on Active Transmission Lines Loaded with Resonant Tunneling Diode Pairs. IEICE Transactions on Electronics, 2012, E95.C, 1385-1388.	0.6	1
38	A Proposal of High-Performance Samplers Based on Resonant Tunneling Diodes. IEICE Transactions on Electronics, 2012, E95.C, 1830-1833.	0.6	4
39	Effects of Initial In Coverage for Preparation of InSb Bilayer on Electrical Properties of InSb Films Grown By Surface Reconstruction Controlled Epitaxy. Japanese Journal of Applied Physics, 2012, 51, 02BH03.	1.5	4
40	Step Hall Measurement of InSb Films Grown on Si(111) Substrate Using InSb Bilayer. Japanese Journal of Applied Physics, 2011, 50, 01BF01.	1.5	6
41	Effects of Deposition Conditions of First InSb Layer on Electrical Properties of n-Type InSb Films Grown With Two-Step Growth Method via InSb Bilayer. Japanese Journal of Applied Physics, 2011, 50, 04DH13.	1.5	10
42	Effects of Deposition Conditions of First InSb Layer on Electrical Properties of n-Type InSb Films Grown With Two-Step Growth Method via InSb Bilayer. Japanese Journal of Applied Physics, 2011, 50, 04DH13.	1.5	5
43	Step Hall Measurement of InSb Films Grown on Si(111) Substrate Using InSb Bilayer. Japanese Journal of Applied Physics, 2011, 50, 01BF01.	1.5	1
44	A Third Order Harmonic Oscillator Based on Coupled Resonant Tunneling Diode Pair Oscillators. IEICE Transactions on Electronics, 2010, E93-C, 1290-1294.	0.6	1
45	Heteroepitaxial growth of InSb films on the patterned Si(001) substrate. Physics Procedia, 2010, 3, 1329-1333.	1.2	3
46	InSb films grown on the V-grooved Si(001) substrate with InSb bilayer. Physics Procedia, 2010, 3, 1335-1339.	1.2	8
47	A traveling wave amplifier based on composite right/left handed (CRLH) transmission lines periodically loaded with resonant tunneling diode pairs. , 2010, , .		2
48	High Quality InSb Films Grown on Si(111) Substrate via InSb Bi-Layer. E-Journal of Surface Science and Nanotechnology, 2009, 7, 145-148.	0.4	15
49	Improved Bias Stability of the Resonant Tunneling Diode Pair Oscillators Integrated on an AlN Ceramic Substrate. Japanese Journal of Applied Physics, 2009, 48, 04C084.	1.5	8
50	Possibility of Terahertz Amplification by Active Transmission Lines Loaded with Resonant Tunneling Diode Pairs. Japanese Journal of Applied Physics, 2009, 48, 124503.	1.5	7
51	Heteroepitaxial growth of a rotated AlInSb layer mediated by an InSb bi-layer on a Si(111) substrate. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 1497-1500.	0.8	2
52	High-temperature growth of heteroepitaxial InSb films on Si(1 1 1) substrate via the InSb bi-layer. Journal of Crystal Growth, 2009, 311, 1692-1695.	1.5	15
53	Heteroepitaxial Growth of InSb Films on V-Grooved Si(001) Substrate. E-Journal of Surface Science and Nanotechnology, 2009, 7, 669-672.	0.4	2
54	Effects of In and Sb mono-layers to form rotated InSb films on a Si(111) substrate. Applied Surface Science, 2008, 254, 6052-6054.	6.1	8

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55	Heteroepitaxial InSb films grown via Si(111)-â^š7Ã—â^š3-In surface reconstruction. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2772-2774.	0.8	9
56	Crystal orientations of InSb films grown on a Si(111) substrate by inserting AlSb buffer layer. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2778-2780.	0.8	0
57	Ultrashort Pulse Generators Using Resonant Tunneling Diodes and Their Integration with Antennas on Ceramic Substrates. Japanese Journal of Applied Physics, 2008, 47, 2833-2837.	1.5	8
58	A GaAs SOI HEMT Fabricated by Fluidic Self-Assembly and Its Application to an RF-Switch. IEICE Transactions on Electronics, 2008, E91-C, 1025-1030.	0.6	2
59	High-Power Oscillations in Resonant Tunneling Diode Pair Oscillator ICs Fabricated with Metamorphic devices. Japanese Journal of Applied Physics, 2007, 46, 2306-2308.	1.5	6
60	Surface Potential Measurement of Carbon Nanotube Field-Effect Transistors Using Kelvin Probe Force Microscopy. Japanese Journal of Applied Physics, 2007, 46, 2496-2500.	1.5	22
61	AlGaN/GaN MIS-HEMTs with HfO2 gate insulator. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 2700-2703.	0.8	38
62	Quasi-normally-off AlGaN/GaN HEMTs fabricated by fluoride-based plasma treatment. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 2732-2735.	0.8	31
63	Dual-clock MASH delta-sigma modulator employing a frequency modulated intermediate signal. IEICE Electronics Express, 2006, 3, 459-463.	0.8	3
64	A new generation of negative-resistance devicesâ€"New developments in ultrahigh-frequency applications based on resonant tunneling elements. Electronics and Communications in Japan, 2006, 89, 29-38.	0.2	4
65	Experimental Demonstration of Ideal Noise Shaping in Resonant Tunneling Deltaâ€"Sigma Modulator for High Resolution, Wide Band Analog-to-Digital Converters. Japanese Journal of Applied Physics, 2006, 45, 3410-3413.	1.5	4
66	Resonant tunnelling delta sigma modulator suitable for high-speed operation. Electronics Letters, 2006, 42, 77.	1.0	12
67	AlGaN/GaN High Electron Mobility Transistors with Inclined-Gate-Recess Structure. Japanese Journal of Applied Physics, 2006, 45, 3368-3371.	1.5	2
68	Controlling high-frequency chaos in resonant tunneling chaos generator circuits. IEICE Electronics Express, 2005, 2, 368-372.	0.8	3
69	Magnetic field effect on the T2 coefficient of the resistivity in the ferromagnetic superconductor UGe2. Physica B: Condensed Matter, 2005, 359-361, 1060-1062.	2.7	1
70	Direct integration of GaAs HEMTs on AlN ceramic substrates using fluidic self-assembly. Electronics Letters, 2005, 41, 1275.	1.0	14
71	Dual-Wavelength High-Power Laser Diodes Fabricated by Selective Fluidic Self-Assembly. Japanese Journal of Applied Physics, 2005, 44, 2568-2571.	1.5	6
72	Metamorphic Resonant Tunneling Diodes and Its Application to Chaos Generator ICs. Japanese Journal of Applied Physics, 2005, 44, 4790-4794.	1.5	5

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73	Deep levels in n-type AlGaN grown by hydride vapor-phase epitaxy on sapphire characterized by deep-level transient spectroscopy. Applied Physics Letters, 2005, 87, 222112.	3.3	39
74	Resonant tunneling diodes and their application to high-speed circuits. , 2005, , .		9
75	Fluid Dynamic Assembly of Semiconductor Blocks for Heterogeneous Integration. Japanese Journal of Applied Physics, 2004, 43, 5951-5954.	1.5	5
76	Surface potential measurements of AlGaNâˆ•GaN high-electron-mobility transistors by Kelvin probe force microscopy. Applied Physics Letters, 2004, 85, 6028-6029.	3.3	19
77	Effects of surface passivation on breakdown of AlGaN/GaN high-electron-mobility transistors. Applied Physics Letters, 2004, 84, 2184-2186.	3.3	124
78	Direct Observation of High-Frequency Chaos Signals from the Resonant Tunneling Chaos Generator. Japanese Journal of Applied Physics, 2004, 43, 5235-5238.	1.5	8
79	Drain Current DLTS of AlGaNâ€“GaN MIS-HEMTs. IEEE Electron Device Letters, 2004, 25, 523-525.	3.9	56
80	A study on current collapse in AlGaN/GaN HEMTs induced by bias stress. IEEE Transactions on Electron Devices, 2003, 50, 2015-2020.	3.0	212
81	Drain current DLTS of AlGaN/GaN HEMTs. Physica Status Solidi A, 2003, 200, 195-198.	1.7	48
82	Study on off-state breakdown in AlGaN/GaN HEMTs. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 2335-2338.	0.8	18
83	Temperature Distributions in AlGaN/GaN HEMTs Measured by Micro-Raman Scattering Spectroscopy. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 57-60.	0.8	4
84	Spin fluctuations and non-Fermi-liquid behavior ofCeNi2Ge2. Physical Review B, 2003, 68, .	3.2	22
85	Measurement of Frequency Dispersion of AlGaN/GaN High Electron Mobility Transistors. Japanese Journal of Applied Physics, 2003, 42, 424-425.	1.5	11
86	AlGaN/GaN Heterostructure Metal-Insulator-Semiconductor High-Electron-Mobility Transistors with Si3N4Gate Insulator. Japanese Journal of Applied Physics, 2003, 42, 2278-2280.	1.5	51
87	Fabricated on a GaAs-based Semiconductor-on-Insulator Substrate Using a Spin-On Low-kDielectric Film. Japanese Journal of Applied Physics, 2003, 42, 6839-6840.	1.5	0
88	Comparison of Electrical Characteristics of Metamorphic HEMTs with InP HEMTs and PHEMTs. Japanese Journal of Applied Physics, 2003, 42, 2219-2222.	1.5	3
89	Characterization of Electrical Properties of Micro-Schottky Contacts on Epitaxial Lateral Overgrowth GaN. Japanese Journal of Applied Physics, 2003, 42, 2250-2253.	1.5	3
90	88â€…GHz dynamic 2:1 frequency divider using resonant tunnelling chaos circuit. Electronics Letters, 2003, 39, 1546.	1.0	27

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91	Fluidic Assembly of Thin GaAs Blocks on Si Substrates. Japanese Journal of Applied Physics, 2003, 42, 2226-2229.	1.5	21
92	Position-Controlled Carbon Nanotube Field-Effect Transistors Fabricated by Chemical Vapor Deposition Using Patterned Metal Catalyst. Japanese Journal of Applied Physics, 2003, 42, 4116-4119.	1.5	50
93	Experimental Demonstration of Capacitor-Coupled Resonant Tunneling Logic Gates for Ultra-short Gate-delay Operation. Japanese Journal of Applied Physics, 2003, 42, 6766-6771.	1.5	1
94	Magnetic phase diagram and the pressure and field dependence of the Fermi surface inUGe2. Physical Review B, 2002, 65, .	3.2	24
95	Electroluminescence in AlGaN/GaN High Electron Mobility Transistors under High Bias Voltage. Japanese Journal of Applied Physics, 2002, 41, 1990-1991.	1.5	13
96	Temperature Distribution Measurement in AlGaN/GaN High-Electron-Mobility Transistors by Micro-Raman Scattering Spectroscopy. Japanese Journal of Applied Physics, 2002, 41, L452-L454.	1.5	21
97	Large Gate Leakage Current in AlGaN/GaN High Electron Mobility Transistors. Japanese Journal of Applied Physics, 2002, 41, 5125-5126.	1.5	64
98	High-Speed Operation of a Novel Frequency Divider Using Resonant Tunneling Chaos Circuit. Japanese Journal of Applied Physics, 2002, 41, 1150-1153.	1.5	11
99	50â€…GHz frequency divider using resonant tunnelling chaos circuit. Electronics Letters, 2002, 38, 305.	1.0	13
100	Current Collapse in AlGaN/GaN HEMTs Investigated by Electrical and Optical Characterizations. Physica Status Solidi A, 2002, 194, 447-451.	1.7	35
101	Effects of the HEMT parameters on the operation frequency of resonant tunneling logic gate MOBILE. Electronics and Communications in Japan, 2002, 85, 1-6.	0.2	3
102	Current Collapse in AlGaN/GaN HEMTs Investigated by Electrical and Optical Characterizations. , 2002, 194, 447.		1
103	Resonant-Tunneling-Injection Photoluminescence of Single InAs Self-Assembled Quantum Dots Embedded in a Thin AlGaAs Barrier. Japanese Journal of Applied Physics, 2001, 40, 2065-2068.	1.5	0
104	A Delta-Sigma Analog-to-Digital Converter Using Resonant Tunneling Diodes. Japanese Journal of Applied Physics, 2001, 40, L1005-L1007.	1.5	11
105	Photoluminescence Study of Resonant Tunneling Transistor with p+/n-Junction Gate. Japanese Journal of Applied Physics, 2000, 39, 35-40.	1.5	3
106	Superconductivity, upper critical field and normal state resistivity in CeNi2Ge2under pressure. Journal of Physics Condensed Matter, 2000, 12, 1339-1349.	1.8	19
107	Robust Operation of a Novel Frequency Divider Using Resonant Tunneling Chaos Circuit. Japanese Journal of Applied Physics, 2000, 39, 3334-3338.	1.5	14
108	Observation of resonant tunneling through single self-assembled InAs quantum dots using electrophotoluminescence spectroscopy. Journal of Applied Physics, 2000, 87, 4332-4336.	2.5	4

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109	Evaluation of effective electron velocity in AlGaN/GaN HEMTs. Electronics Letters, 2000, 36, 1736.	1.0	31
110	Measurements of Electroluminescence Intensity Distribution in the Direction of Gate Width of n+Self-Aligned Gate GaAs Metal-Semiconductor Field-Effect Transistors. Japanese Journal of Applied Physics, 1999, 38, 1363-1364.	1.5	4
111	Highly Uniform Regrown In0.53Ga0.47As/AlAs/InAs Resonant Tunneling Diodes on In0.53Ga0.47As. Japanese Journal of Applied Physics, 1999, 38, 1204-1207.	1.5	8
112	Resonant Tunneling Chaos Generator for High-Speed/Low-Power Frequency Divider. Japanese Journal of Applied Physics, 1999, 38, L1321-L1322.	1.5	16
113	Optoelectronic Flexible-Function Logic Gate Using Monostable-Bistable Transition of Serially Connected Resonant Tunneling Transistors. Japanese Journal of Applied Physics, 1999, 38, 2586-2589.	1.5	0
114	Measurement of Contact Potential of GaAs pn Junctions by Kelvin Probe Force Microscopy. Japanese Journal of Applied Physics, 1999, 38, 4893-4894.	1.5	19
115	Potential profile measurement of GaAs MESFETs passivated with low-temperature grown GaAs layer by Kelvin probe force microscopy. Solid-State Electronics, 1999, 43, 1547-1553.	1.4	14
116	Large-signal microwave characteristics of resonant-tunneling high electron mobility transistors. IEEE Transactions on Electron Devices, 1999, 46, 281-287.	3.0	5
117	Measurement of Contact Potential of GaAs/AlGaAs Heterostructure Using Kelvin Probe Force Microscopy. Japanese Journal of Applied Physics, 1999, 38, L767-L769.	1.5	11
118	High-speed and low-power operation of a resonant tunneling logic gate MOBILE. IEEE Electron Device Letters, 1998, 19, 80-82.	3.9	113
119	Sampling phase detector using a resonant tunneling high electron mobility transistor for microwave phase-locked oscillators. IEEE Transactions on Very Large Scale Integration (VLSI) Systems, 1998, 6, 39-42.	3.1	2
120	A Large Output Voltage Swing of a Resonant Tunneling Flip-Flop Circuit Employing a Monostable-Bistable Transition Logic Element (MOBILE). Japanese Journal of Applied Physics, 1998, 37, L1286-L1287.	1.5	4
121	A Novel Delayed Flip-Flop Circuit Using Resonant Tunneling Logic Gates. Japanese Journal of Applied Physics, 1998, 37, L212-L213.	1.5	11
122	Uniformity of the High Electron Mobility Transistors and Resonant Tunneling Diodes Integrated on an InP Substrate Using an Epitaxial Structure Grown by Molecular Beam Epitaxy and Metalorganic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 1998, 37, 5500-5502.	1.5	11
123	High-speed operation of static binary frequency divider using resonant tunnelling diodes and HEMTs. Electronics Letters, 1998, 34, 70.	1.0	22
124	Resistive-fuse network for early vision using resonant tunnelling diodes and HEMTs on an InP substrate. Electronics Letters, 1997, 33, 722.	1.0	2
125	Static frequency divider featuring reduced circuit complexity by utilizing resonant tunneling diodes in combination with HEMTs. IEEE Electron Device Letters, 1997, 18, 544-546.	3.9	16
126	High-frequency small-signal and large-signal characteristics of resonant tunneling high electron mobility transistors (RTHEMTs). IEEE Transactions on Electron Devices, 1997, 44, 2038-2040.	3.0	3

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127	High-speed operation of resonant tunnelling flip-flop circuit employing MOBILE (monostable-bistable) Tj ETQq1 1 0.784314 rgBT /Ove	1.0	17
128	High-pressure resistivity and lattice parameters of CeNi2Ge2. Physica B: Condensed Matter, 1997, 230-232, 198-200.	2.7	13
129	A highly mismatched InxGa1â^'xAs/AlGaAs (0 â‰¦ x â‰¦ 0.5) pseudomorphic HEMT on GaAs substrate using an Inx/2Ga1â^'x/2As buffer layer. Solid-State Electronics, 1997, 41, 1469-1474.	1.4	1
130	InP-based high-performance monostable-bistable transition logic elements (MOBILEs) using integrated multiple-input resonant-tunneling devices. IEEE Electron Device Letters, 1996, 17, 127-129.	3.9	124
131	An exclusive-OR logic circuit based on controlled quenching of series-connected negative differential resistance devices. IEEE Electron Device Letters, 1996, 17, 309-311.	3.9	34
132	High-performance InP-based enhancement-mode HEMTs using non-alloyed ohmic contacts and Pt-based buried-gate technologies. IEEE Transactions on Electron Devices, 1996, 43, 252-257.	3.0	123
133	InP-Based High-Performance Monostable-Bistable Transition Logic Element (MOBILE): an Intelligent Logic Gate Featuring Weighted-Sum Threshold Operations. Japanese Journal of Applied Physics, 1996, 35, 1172-1177.	1.5	18
134	Improved source resistance in InP-based enhancement-mode HEMTs for high speed digital applications. Electronics Letters, 1995, 31, 925-927.	1.0	15
135	Novel currentâ€“voltage characteristics in an InPâ€based resonantâ€tunneling high electron mobility transistor. Applied Physics Letters, 1995, 67, 3608-3610.	3.3	27
136	Monostable-Bistable Transition Logic Elements (MOBILEs) Based on Monolithic Integration of Resonant Tunneling Diodes and FETs. Japanese Journal of Applied Physics, 1995, 34, 1199-1203.	1.5	20
137	Analysis of Switching Time of Monostable-Bistable Transition Logic Elements Based on Simple Model Calculation. Japanese Journal of Applied Physics, 1995, 34, 1213-1217.	1.5	17
138	Monolithic integration of resonant tunneling diodes and FET's for monostable-bistable transition logic elements (MOBILE's). IEEE Electron Device Letters, 1995, 16, 70-73.	3.9	44
139	More flexible and simpler logic circuits implemented with resonant tunneling transistors. IEEE Transactions on Electron Devices, 1995, 42, 1005-1007.	3.0	4
140	Threshold Logic Function on Both Positive and Negative Weighted Sums in Multiple-Input Monostable-Bistable Transition Logic Elements. Japanese Journal of Applied Physics, 1994, 33, 794-797.	1.5	5
141	X conduction two-dimensional subband structure and order in AlGaAs/AlAs quantum wells. Physica B: Condensed Matter, 1994, 201, 295-300.	2.7	9
142	Functions and applications of monostable-bistable transition logic elements (MOBILE's) having multiple-input terminals. IEEE Transactions on Electron Devices, 1994, 41, 148-154.	3.0	107
143	X-conduction-electron transport in very thin AlAs quantum wells. Physical Review B, 1994, 49, 2189-2192.	3.2	15
144	Reset-set flipflop based on a novel approach of modulating resonant-tunnelling current with FET gates. Electronics Letters, 1994, 30, 1805-1806.	1.0	9

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145	Clear negative characteristics observed in coupled-quantum-well base resonant tunneling transistors. IEEE Electron Device Letters, 1993, 14, 202-204.	3.9	5
146	Weighted sum threshold logic operation of MOBILE (monostable-bistable transition logic element) using resonant-tunneling transistors. IEEE Electron Device Letters, 1993, 14, 475-477.	3.9	69
147	A New Resonant Tunneling Logic Gate Employing Monostable-Bistable Transition. Japanese Journal of Applied Physics, 1993, 32, L42-L44.	1.5	130
148	Monte Carlo Study of Charge Injection Transistors (CHINTs). Japanese Journal of Applied Physics, 1993, 32, 26-30.	1.5	18
149	Monte Carlo Simulation of Response Time for Velocity Modulation Transistors. Japanese Journal of Applied Physics, 1992, 31, 757-760.	1.5	4
150	Identification of Vacancy-Type Defects in Molecular Beam Epitaxy-Grown GaAs Using a Slow Positron Beam. Japanese Journal of Applied Physics, 1992, 31, 2056-2060.	1.5	2
151	Effective mass and ground state of AlAs quantum wells studied by magnetoresistance measurements. Journal of Applied Physics, 1992, 71, 296-299.	2.5	24
152	Temperature dependence of high-frequency performance of AlGaAs/InGaAs pseudomorphic HEMT's. IEEE Electron Device Letters, 1992, 13, 8-10.	3.9	23
153	Analysis of microwave characteristics of a double-channel FET employing the velocity-modulation transistor concept. IEEE Transactions on Electron Devices, 1992, 39, 2438-2443.	3.0	2
154	High-Frequency Characteristics of Charge-Injection Transistor-Mode Operation in AlGaAs/InGaAs/GaAs Metal-Insulator-Semiconductor Field-Effect Transistors. Japanese Journal of Applied Physics, 1991, 30, 1190-1193.	1.5	17
155	Resonant Tunneling in a Novel Coupled-Quantum-Well Base Transistor. Japanese Journal of Applied Physics, 1991, 30, L2018-L2020.	1.5	20
156	Characterization of Lattice Sites and Compensation Mechanism in Heavily Si-Doped GaAs with Laser Raman Spectroscopy. Japanese Journal of Applied Physics, 1990, 29, 301-304.	1.5	9
157	Magnetic properties and Fermi surface of antiferromagneticSmCu6. Physical Review B, 1990, 41, 568-572.	3.2	10
158	Optically excited minorityâ€electron velocity in selectively Beâ€doped AlGaAs/GaAs/AlGaAs single quantum wells. Applied Physics Letters, 1990, 56, 1146-1148.	3.3	7
159	Compensation Mechanism in Heavily Si-Doped GaAs Grown by MBE. Japanese Journal of Applied Physics, 1990, 29, L527-L529.	1.5	18
160	An AlGaAs/In/sub x/Ga/sub 1-x/As/AlGaAs (0>or=x>or=0.5) pseudomorphic HEMT on GaAs substrate using an In/sub x/2/Ga/sub 1-x/2/As buffer layer. IEEE Transactions on Electron Devices, 1990, 37, 1416-1421.	3.0	6
161	Improvement of Ge/AlGaAs Air-Exposed Interfaces Grown by MBE and Their Application to n+-Ge Gate AlGaAs/GaAs MISFETs. Japanese Journal of Applied Physics, 1989, 28, 748-753.	1.5	0
162	Submicrometer n/sup +/-Ge gate AlGaAs/GaAs MISFETs. IEEE Transactions on Electron Devices, 1989, 36, 2217-2222.	3.0	10

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